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Lead-free Green

2N7002DWK

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
60V	3.0Ω @ V_{GS} = 10V	261mA
	4.0Ω @ V_{GS} = 4.5V	226mA

Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Power Management Functions

Mechanical Data

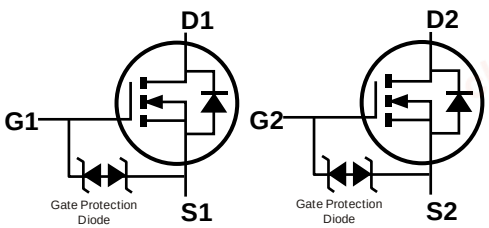
- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead-Free Plating). Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



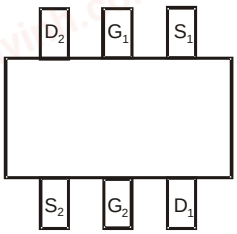
SOT363



Top View



Equivalent Circuit



Top View
Internal Schematic

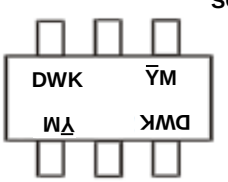
Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002DWK-7	SOT363	3,000/Tape & Reel
2N7002DWK-13	SOT363	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

SOT363



DWK = Product Type Marking Code
$\overline{Y}$M = Date Code Marking
$\overline{Y}$ = Year (ex: H = 2020)
M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	H	I	J	K	L	M	N	O	P	R	S	T

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	261 208	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	261	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	1.1	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	1.1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.33	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	379	°C/W
Total Power Dissipation (Note 6)		P_D	0.45	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	278	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	—	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.3 1.5	3.0 4.0	Ω	V_{GS} = 10V, I_D = 200mA V_{GS} = 4.5V, I_D = 150mA
Diode Forward Voltage	V_{SD}	—	0.8	1.4	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	41	—	pF	V_{DS} = 30V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	4.5	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.7	—	pF	
Gate Resistance	R_g	—	224	—	Ω	f = 1MHz , V_{GS} = 0V, V_{DS} = 0V
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	0.51	—	nC	V_{DS} = 15V, I_D = 200mA
Total Gate Charge (V_{GS} = 10V)	Q_g	—	1.04	—	nC	
Gate-Source Charge	Q_{gs}	—	0.16	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.18	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	6.9	—	ns	V_{DD} = 30V, V_{GS} = 10V, R_G = 150Ω, I_D = 200mA
Turn-On Rise Time	t_R	—	5.8	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	37.8	—	ns	
Turn-Off Fall Time	t_F	—	14.3	—	ns	
Reverse Recovery Time	t_{RR}	—	88	—	ns	I_F = 1A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	29	—	nC	I_F = 1A, di/dt = 100A/µs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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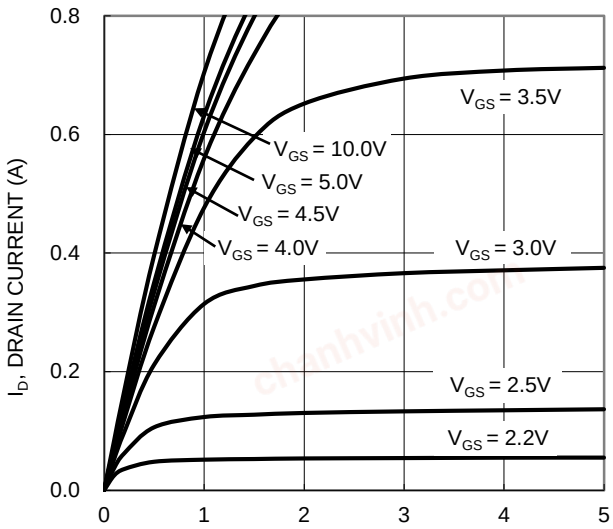


Figure 1. Typical Output Characteristic

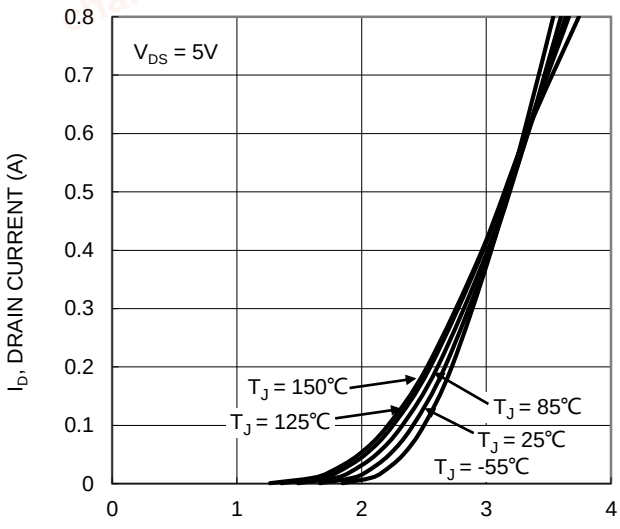


Figure 2. Typical Transfer Characteristic

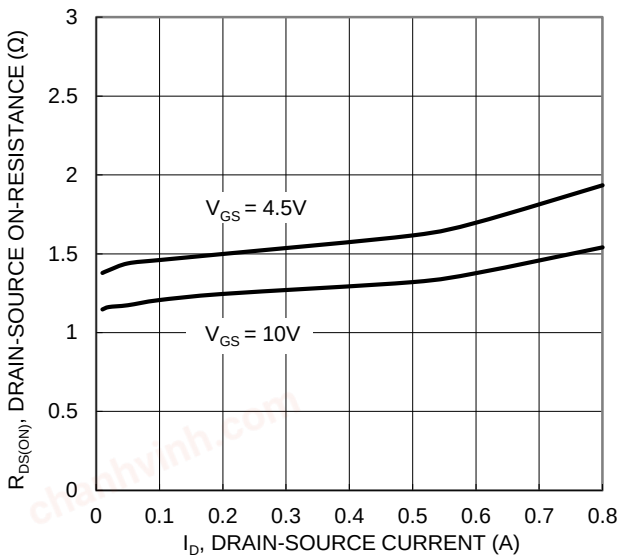


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

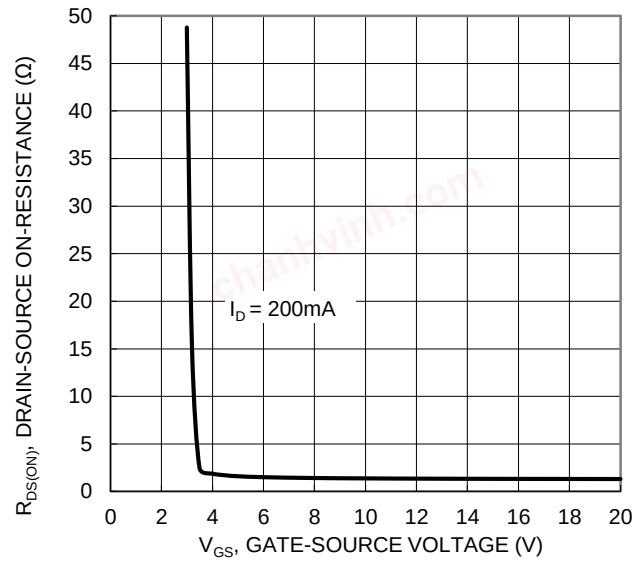


Figure 4. Typical Transfer Characteristic

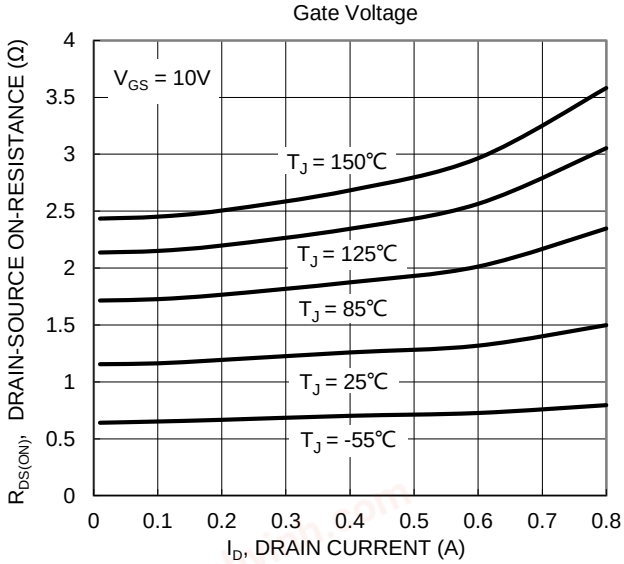


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

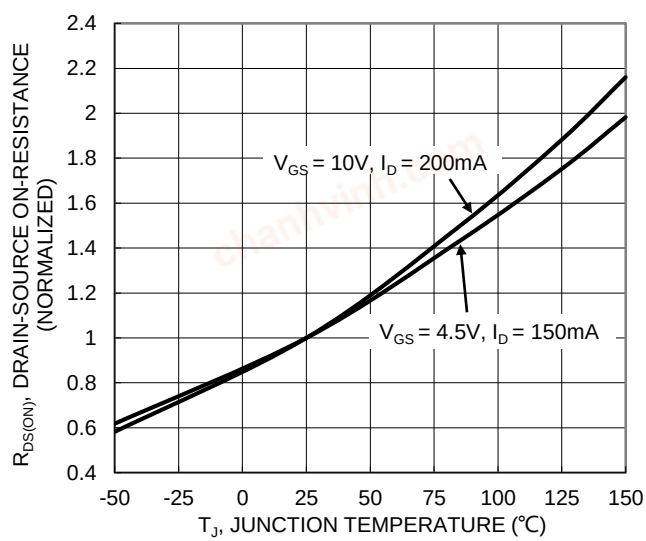


Figure 6. On-Resistance Variation with Junction Temperature

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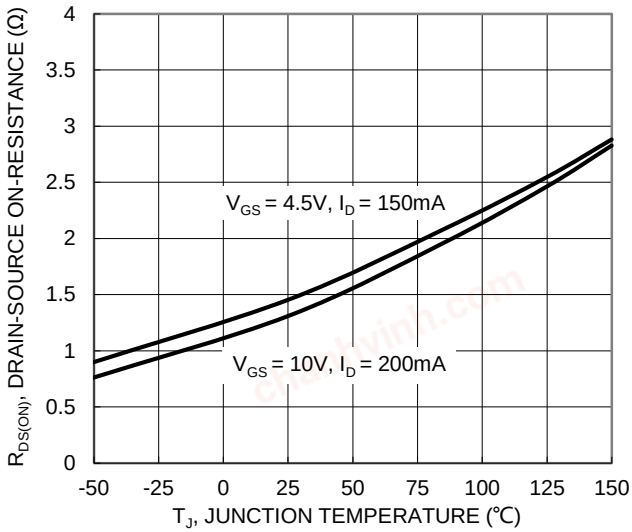


Figure 7. On-Resistance Variation with Junction Temperature

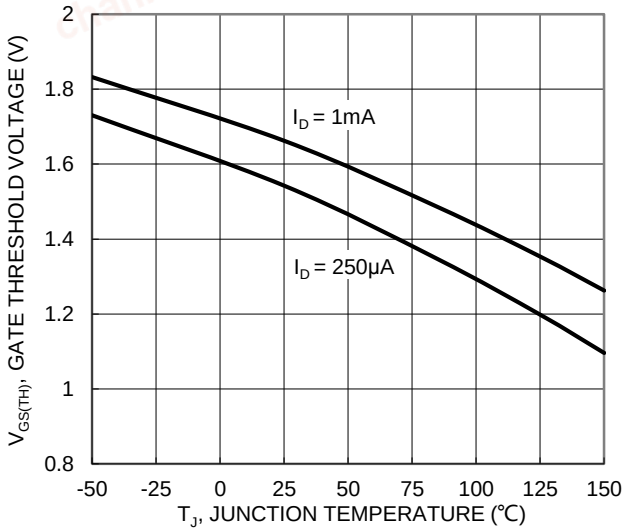


Figure 8. Gate Threshold Variation vs. Junction Temperature

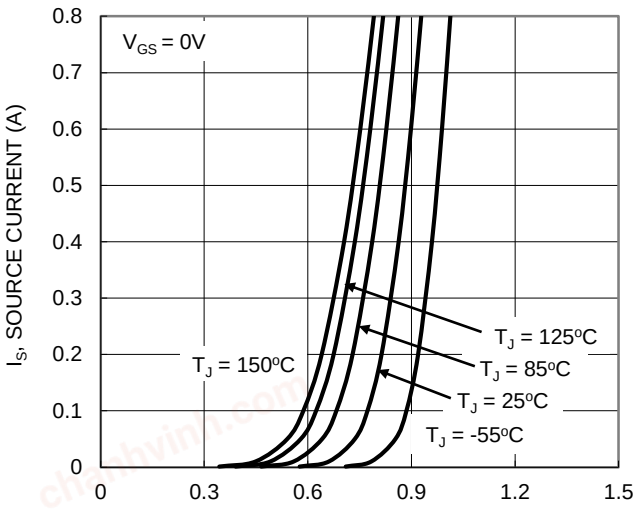


Figure 9. Diode Forward Voltage vs. Current

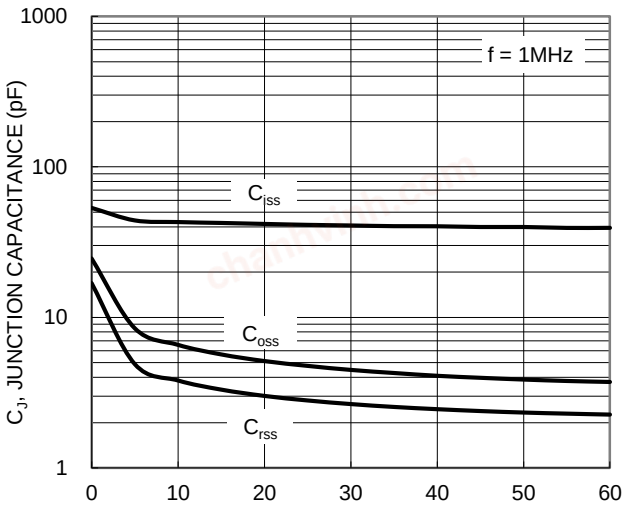


Figure 10. Typical Junction Capacitance

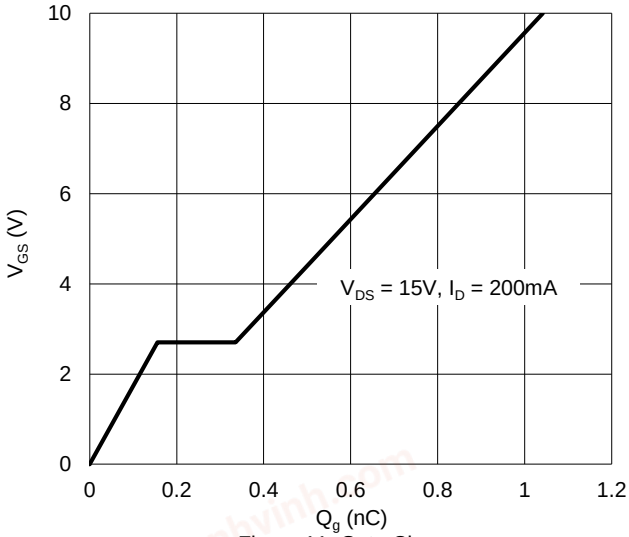


Figure 11. Gate Charge

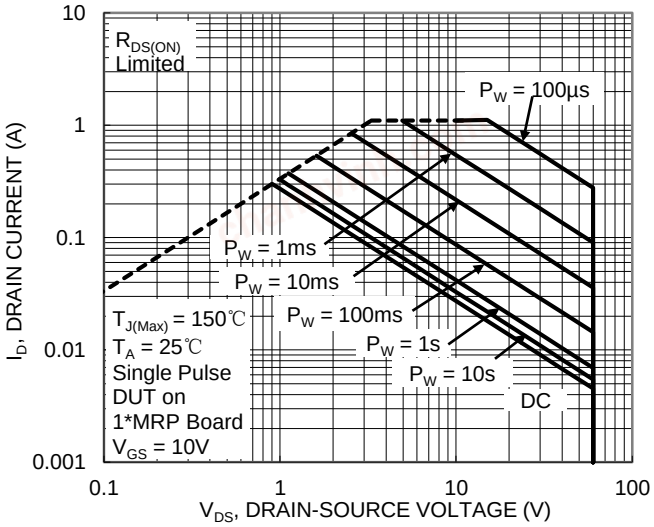


Figure 12. SOA, Safe Operation Area

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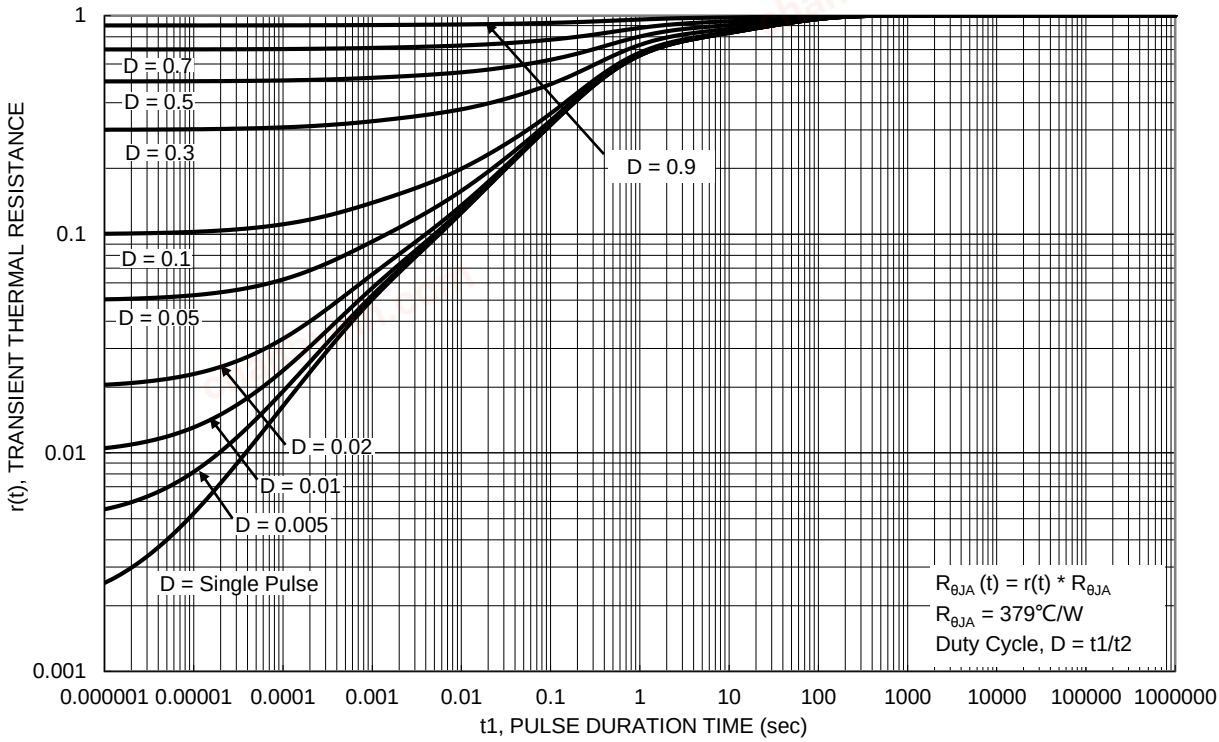


Figure 13. Transient Thermal Resistance

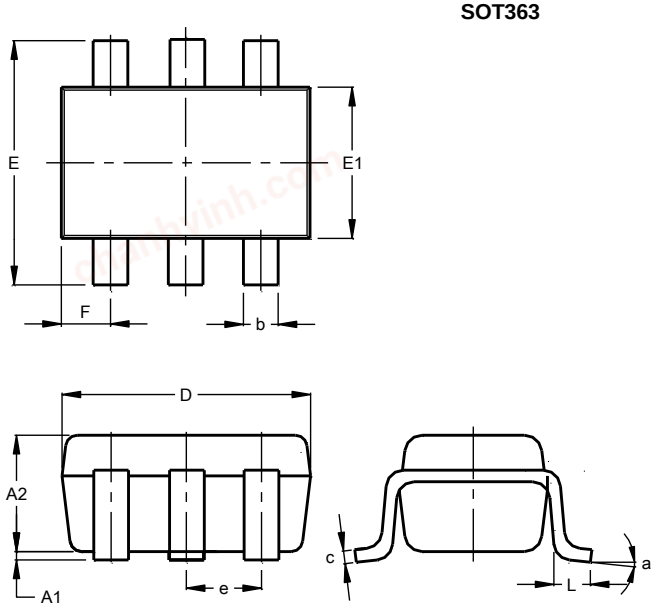
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363

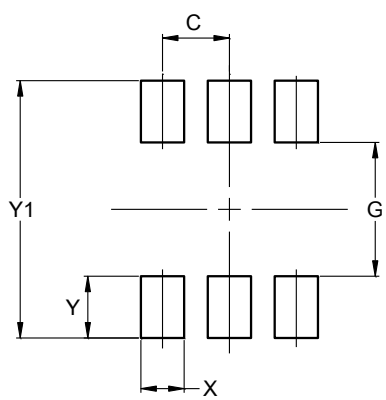


SOT363			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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